

Title (en)

Method of manufacturing transistor, and of electronic device including transistor

Title (de)

Verfahren zur Herstellung eines Transistors und einer einen Transistor enthaltenden elektronischen Vorrichtung

Title (fr)

Procédé de fabrication de transistor et de dispositif électronique incluant le transistor

Publication

EP 2339633 B1 20160810 (EN)

Application

EP 10167614 A 20100629

Priority

KR 20090129127 A 20091222

Abstract (en)

[origin: EP2339633A1] Provided are a transistor, a method of manufacturing the transistor, and an electronic device including the transistor. The transistor may include a gate insulator of which at least one surface is treated with plasma. The surface of the gate insulator may be an interface that contacts a channel layer. The interface may be treated with plasma by using a fluorine (F)-containing gas, and thus may include fluorine (F). The interface treated with plasma may suppress the characteristic variations of the transistor due to light.

IPC 8 full level

H01L 29/49 (2006.01); **H01L 29/66** (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP KR US)

H01L 29/1025 (2013.01 - KR); **H01L 29/41725** (2013.01 - KR); **H01L 29/4232** (2013.01 - KR); **H01L 29/4908** (2013.01 - EP US); **H01L 29/66969** (2013.01 - EP US); **H01L 29/7869** (2013.01 - EP KR US); **H01L 29/78696** (2013.01 - EP US)

Citation (examination)

US 2009294764 A1 20091203 - KIM CHANG-JUNG [KR], et al

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)

EP 2339633 A1 20110629; **EP 2339633 B1 20160810**; CN 102104072 A 20110622; CN 102104072 B 20150930; KR 101603768 B1 20160315; KR 20110072270 A 20110629; US 2011147734 A1 20110623; US 8354670 B2 20130115

DOCDB simple family (application)

EP 10167614 A 20100629; CN 201010227417 A 20100712; KR 20090129127 A 20091222; US 80153110 A 20100614